

NCV4279A

5.0 V Micropower 150 mA LDO Linear Regulator with DELAY, Adjustable RESET, and Sense Output

The NCV4279A is a 5.0 V precision micropower voltage regulator with an output current capability of 150 mA.

The output voltage is accurate within $\pm 2.0\%$ with a maximum dropout voltage of 0.5 V at 100 mA. Low quiescent current is a feature drawing only 150 μA with a 1.0 mA load. This part is ideal for any and all battery operated microprocessor equipment.

Microprocessor control logic includes an active reset output RO with delay and a SI/SO monitor which can be used to provide an early warning signal to the microprocessor of a potential impending reset signal. The use of the SI/SO monitor allows the microprocessor to finish any signal processing before the reset shuts the microprocessor down.

The active Reset circuit operates correctly at an output voltage as low as 1.0 V. The Reset function is activated during the power up sequence or during normal operation if the output voltage drops outside the regulation limits.

The reset threshold voltage can be decreased by the connection of an external resistor divider to the R_{ADJ} lead. The regulator is protected against reverse battery, short circuit, and thermal overload conditions. The device can withstand load dump transients making it suitable for use in automotive environments. The device has also been optimized for EMC conditions.

If the application requires pullup resistors at the logic outputs Reset and Sense Out, the NCV4269A with integrated resistors can be used.

Features

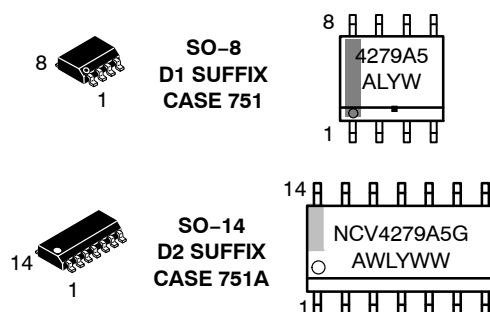
- 5.0 V $\pm 2.0\%$ Output
- Low 150 μA Quiescent Current
- Active Reset Output Low Down to $V_Q = 1.0$ V
- Adjustable Reset Threshold
- 150 mA Output Current Capability
- Fault Protection
 - ◆ +60 V Peak Transient Voltage
 - ◆ -40 V Reverse Voltage
 - ◆ Short Circuit
 - ◆ Thermal Overload
- Early Warning through SI/SO Leads
- Internally Fused Leads in SO-14 Package
- Very Low Dropout Voltage
- Electrical Parameters Guaranteed Over Entire Temperature Range
- These are Pb-Free Devices
- NCV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable



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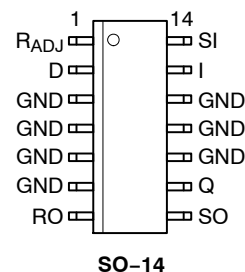
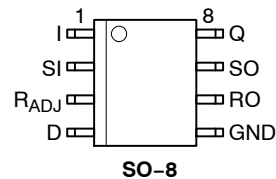
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MARKING DIAGRAMS



A = Assembly Location
WL, L = Wafer Lot
YY, Y = Year
WW, W = Work Week
■, G = Lead Free Indicators

PIN CONNECTIONS



ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 13 of this data sheet.

NCV4279A

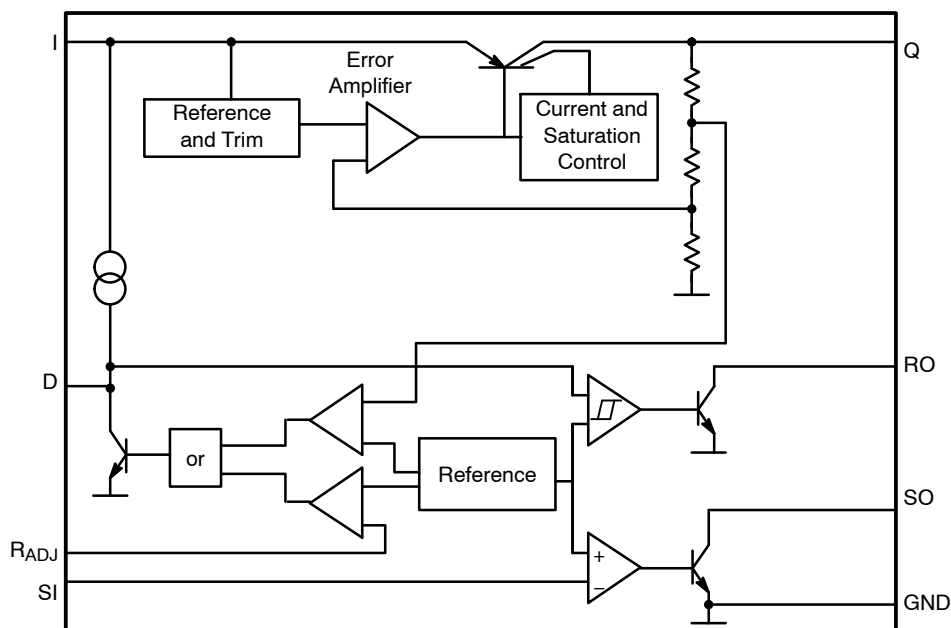


Figure 1. Block Diagram

PACKAGE PIN DESCRIPTION

Package Pin Number		Pin Symbol	Function
SO-8	SO-14		
3	1	R _{ADJ}	Reset Threshold Adjust; if not used to connect to GND.
4	2	D	Reset Delay; To Set Time Delay, Connect to GND with a Capacitor
5	3, 4, 5, 6, 10, 11, 12	GND	Ground
6	7	RO	Reset Output; This is an Open-Collector Output. Leave Open if Not Used.
7	8	SO	Sense Output; This is an Open-Collector Output. If not used, keep open.
8	9	Q	5 V Output; Connect to GND with a 10 μ F Capacitor, ESR < 10 Ω .
1	13	I	Input; Connect to GND Directly at the IC with a Ceramic Capacitor.
2	14	SI	Sense Input; If not used, Connect to Q.

NCV4279A

MAXIMUM RATINGS ($T_J = -40^{\circ}\text{C}$ to 150°C)

Parameter	Symbol	Min	Max	Unit
Input to Regulator	V_I I_I	-40 Internally Limited	45 Internally Limited	V
Input Peak Transient Voltage	V_I	-	60	V
Sense Input	V_{SI} I_{SI}	-40 -1	45 1	V mA
Reset Threshold Adjust	V_{RADJ} I_{RADJ}	-0.3 -10	7 10	V mA
Reset Delay	V_D I_D	-0.3 Internally Limited	7 Internally Limited	V
Ground	I_q	50	-	mA
Reset Output	V_{RO} I_{RO}	-0.3 Internally Limited	7 Internally Limited	V
Sense Output	V_{SO} I_{SO}	-0.3 Internally Limited	7 Internally Limited	V
Regulated Output	V_Q I_Q	-0.5 -10	7.0 -	V mA
Junction Temperature	T_J	-	150	$^{\circ}\text{C}$
Storage Temperature	T_{STG}	-50	150	$^{\circ}\text{C}$
Input Voltage Operating Range	V_I	-	45	V
Junction Temperature Operating Range	T_J	-40	150	$^{\circ}\text{C}$

LEAD TEMPERATURE SOLDERING AND MSL

Parameter	Symbol	Value	Unit
MSL, 8-Lead, 14-Lead, LS Temperature 260°C Peak (Notes 3)	MSL	1	-

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

- This device series incorporates ESD protection and exceeds the following ratings:
Human Body Model (HBM) ≤ 4.0 kV per AEC-Q100-002.
Machine Model (MM) ≤ 200 V per AEC-Q100-003.
- Latchup Current Maximum Rating: ≤ 150 mA per AEC-Q100-004.
- Lead free: 60-150 Sec above 217°C , 40 Sec Max at Peak, 265°C Peak.

THERMAL CHARACTERISTICS

Characteristic	Test Conditions (Typical Values)	Unit
SO-8 Package (Note 4)		
Junction-to-Pin 4 ($\Psi - \text{JL4}, \Psi_{L4}$)	53.8	$^{\circ}\text{C/W}$
Junction-to-Ambient Thermal Resistance ($R_{\theta JA}, \theta_{JA}$)	170.9	$^{\circ}\text{C/W}$
SO-14 Package (Note 4)		
Junction-to-Pin 4 ($\Psi - \text{JL4}, \Psi_{L4}$)	18.4	$^{\circ}\text{C/W}$
Junction-to-Ambient Thermal Resistance ($R_{\theta JA}, \theta_{JA}$)	111.6	$^{\circ}\text{C/W}$

- 2 oz copper, 50 mm² copper area, 1.5 mm thick FR4

NCV4279A

ELECTRICAL CHARACTERISTICS (−40°C ≤ T_J ≤ 150°C, V_I = 13.5 V unless otherwise specified)

Characteristic	Symbol	Test Conditions	Min	Typ	Max	Unit
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REGULATOR

Output Voltage	V _Q	1 mA ≤ I _Q ≤ 100 mA; 6 V ≤ V _I ≤ 16 V	4.90	5.00	5.10	V
Current Limit	I _Q	–	150	200	500	mA
Current Consumption; I _q = I _I – I _Q	I _q	I _Q = 1 mA, RO, SO High	–	190	250	μA
Current Consumption; I _q = I _I – I _Q	I _q	I _Q = 1 mA, RO High, SO Low (Note 5)	–	560	650	μA
Current Consumption; I _q = I _I – I _Q	I _q	I _Q = 10 mA, RO, SO High	–	250	450	μA
Current Consumption; I _q = I _I – I _Q	I _q	I _Q = 50 mA, RO, SO High	–	2.0	3.0	mA
Dropout Voltage	V _{dr}	I _Q = 100 mA (Note 6)	–	0.25	0.5	V
Load Regulation	ΔV _Q	I _Q = 5 mA to 100 mA	–	10	20	mV
Line Regulation	ΔV _Q	V _I = 6 V to 26 V; I _Q = 1 mA	–	10	30	mV

RESET GENERATOR

Reset Switching Threshold	V _{RT}	–	4.50	4.65	4.80	V
Reset Adjust Switching Threshold	V _{RADJ,TH}	V _Q > 3.5 V	1.26	1.35	1.44	V
Reset Output Saturation Voltage	V _{RO,SAT}	V _Q < V _{RT} , R _{RO} = 20 kΩ	–	0.1	0.4	V
Upper Delay Switching Threshold	V _{UD}	–	1.4	1.8	2.2	V
Lower Delay Switching Threshold	V _{LD}	–	0.3	0.45	0.60	V
Saturation Voltage on Delay Capacitor	V _{D,SAT}	V _Q < V _{RT}	–	–	0.1	V
Charge Current	I _{D,C}	V _D = 1 V	3.0	6.5	9.5	μA
Delay Time L → H	t _d	C _D = 100 nF	17	28	–	ms
Delay Time H → L	t _{RR}	C _D = 100 nF	–	3.15	–	μs

INPUT VOLTAGE SENSE

Sense Threshold High	V _{SI,High}	–	1.24	1.31	1.38	V
Sense Threshold Low	V _{SI,Low}	–	1.16	1.20	1.28	V
Sense Output Saturation Voltage	V _{SO,Low}	V _{SI} < 1.20 V; V _Q > 3 V; R _{SO} = 20 kΩ	–	0.1	0.4	V
Sense Input Current	I _{SI}	–	–1.0	0.1	1.0	μA

5. Including 20 kΩ external SO pull-up resistor current.

6. Dropout voltage = V_I – V_Q measured when the output voltage has dropped 100 mV from the nominal value obtained at 13.5 V input.

The diagram consists of four vertically stacked waveforms sharing a common time axis t .

- Top waveform (V_I):** Input voltage. It shows a ramp-up, a long plateau, a sharp dip, a ramp-down, and another ramp-up.
- Second waveform (V_Q):** Gate voltage. It follows the input voltage with a delay. Key features include:
 - A rise time labeled t_d .
 - A plateau level labeled V_{RT} .
 - A fall time labeled t_{RR} during a voltage dip at the input.
 - A secondary spike labeled $< t_{RR}$.
- Third waveform (V_D):** Driver voltage. It shows the MOSFET's switching behavior. Key features include:
 - A plateau level labeled V_{UD} .
 - A lower level labeled V_{LD} .
 - A fall time labeled t_{RR} during a voltage dip at the input.
 - A slope during turn-on labeled $\frac{dV}{dt} = \frac{I_D}{C_D}$.
- Bottom waveform (V_{RO}):** Output voltage. It shows the load voltage. Key features include:
 - A saturation level labeled $V_{RO,SAT}$.
 - A sharp drop during a voltage dip at the input.
 - A secondary spike.
 - A drop during an overload event.

Below the V_{RO} waveform, six vertical arrows point to specific events on the time axis:

- Power-on-Reset
- Thermal Shutdown
- Voltage Dip at Input
- Undervoltage
- Secondary Spike
- Overload at Output

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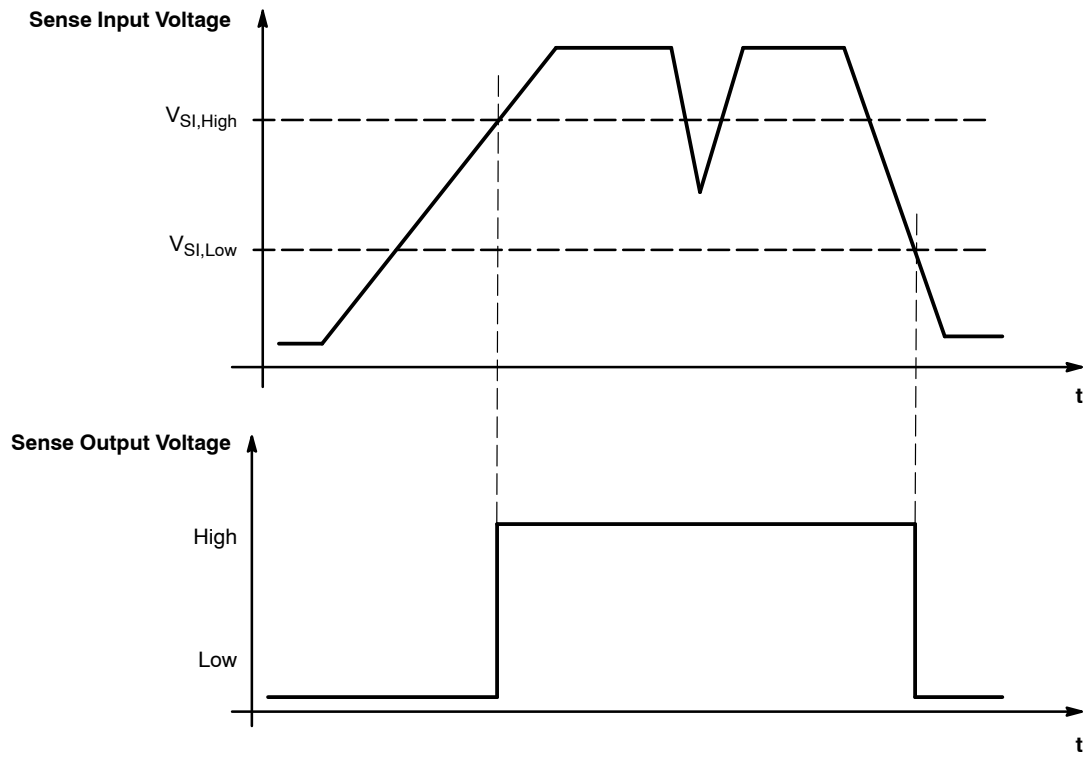


Figure 4. Sense Timing Diagram

TYPICAL PERFORMANCE CHARACTERISTICS

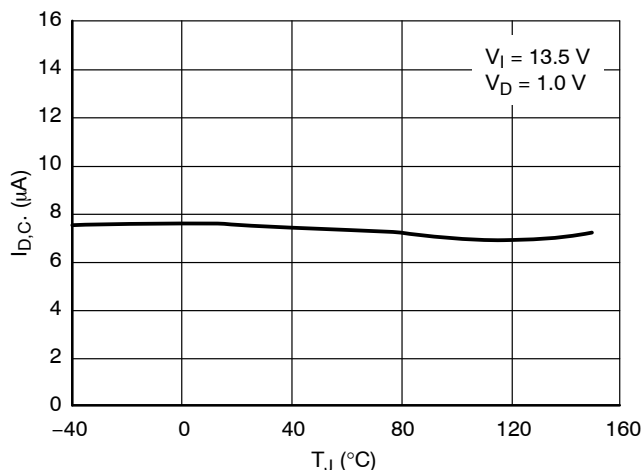


Figure 5. Charge Current $I_{D,C}$ vs. Temperature T_J

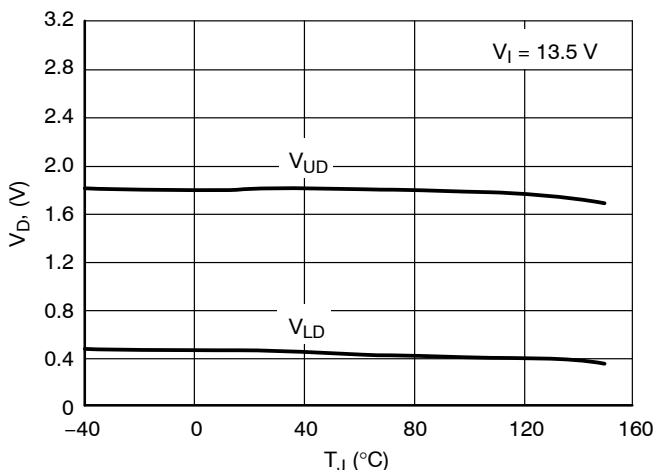


Figure 6. Switching Voltage V_{UD} and V_{LD} vs. Temperature T_J

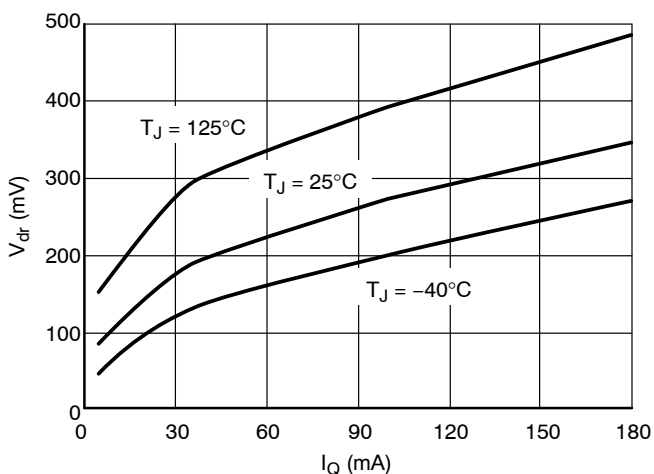


Figure 7. Drop Voltage V_{dr} vs. Output Current I_Q

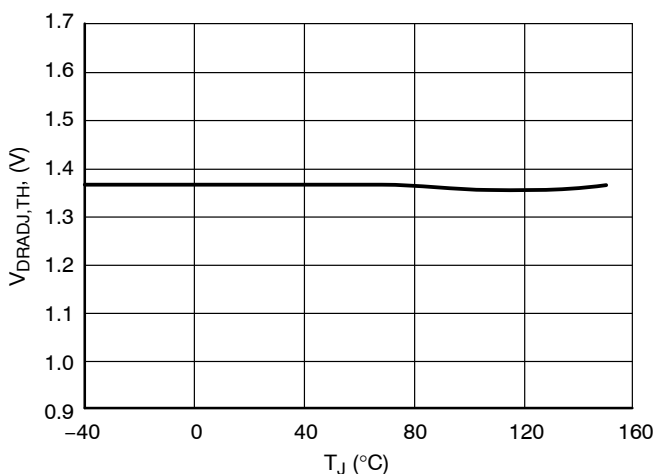


Figure 8. Reset Adjust Switching Threshold $V_{RADJ,TH}$ vs. Temperature T_J

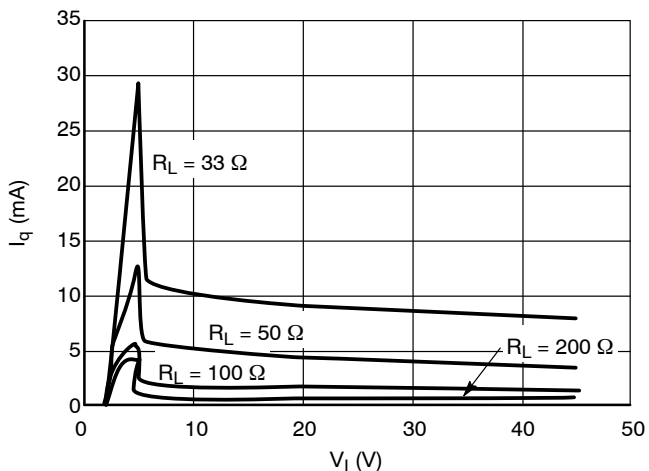


Figure 9. Current Consumption I_q vs. Input Voltage V_I

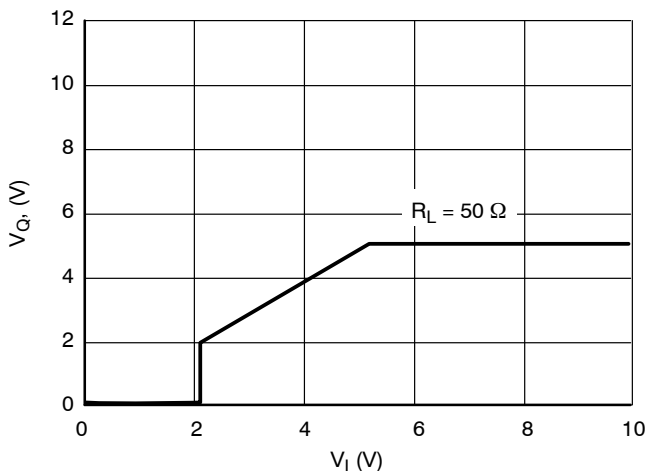


Figure 10. Output Voltage V_Q vs. Input Voltage V_I

TYPICAL PERFORMANCE CHARACTERISTICS

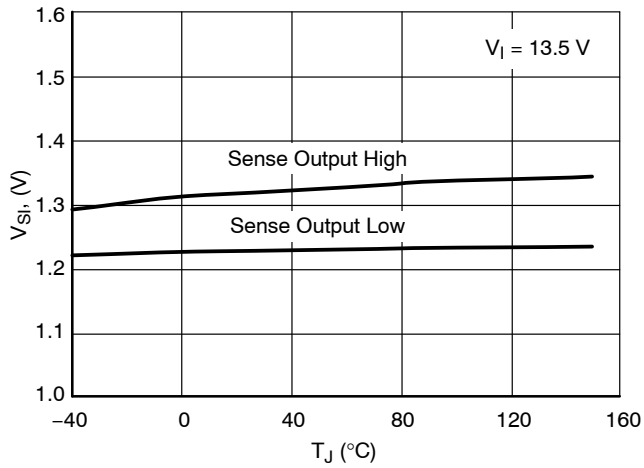


Figure 11. Sense Threshold V_{Sl} vs. Temperature T_J

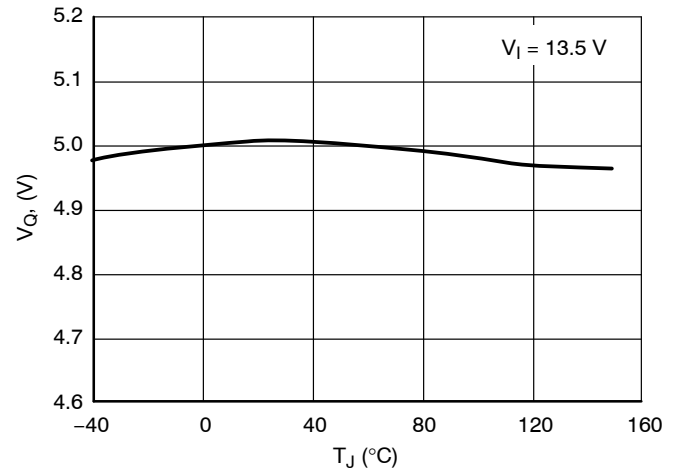


Figure 12. Output Voltage V_Q vs. Temperature T_J

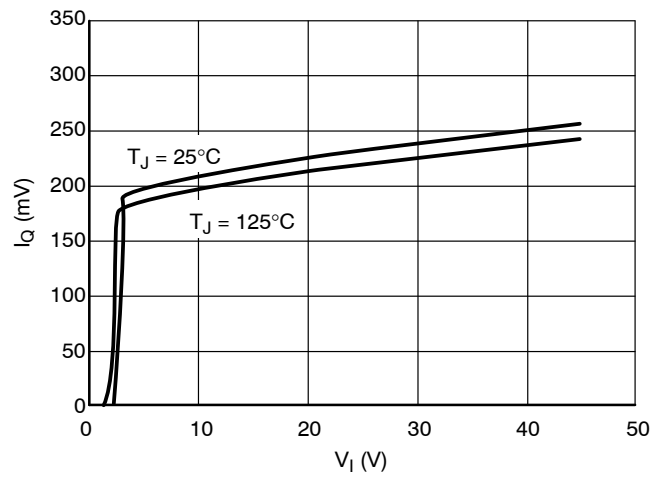


Figure 13. Output Current I_Q vs. Input Voltage V_I

TYPICAL PERFORMANCE CHARACTERISTICS

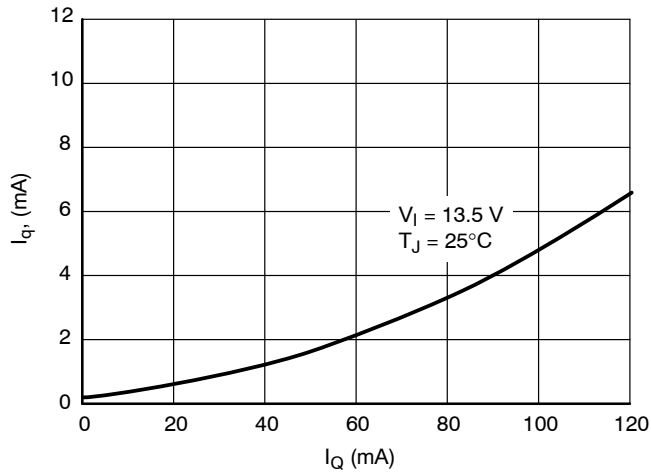


Figure 14. Current Consumption I_Q vs. Output Current I_Q

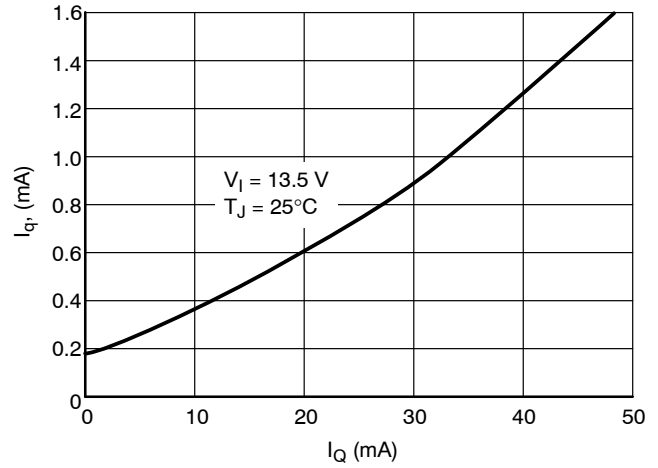


Figure 15. Current Consumption I_Q vs. Output Current I_Q

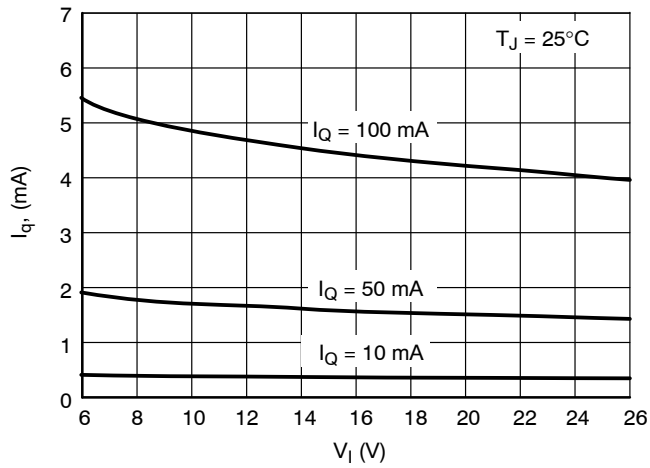


Figure 16. Current Consumption I_Q vs. Input Voltage V_I

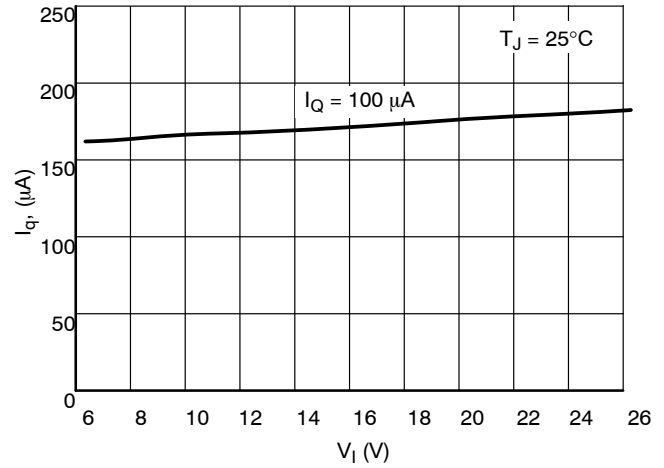


Figure 17. Current Consumption I_Q vs. Input Voltage V_I

NCV4279A

TYPICAL THERMAL CHARACTERISTICS

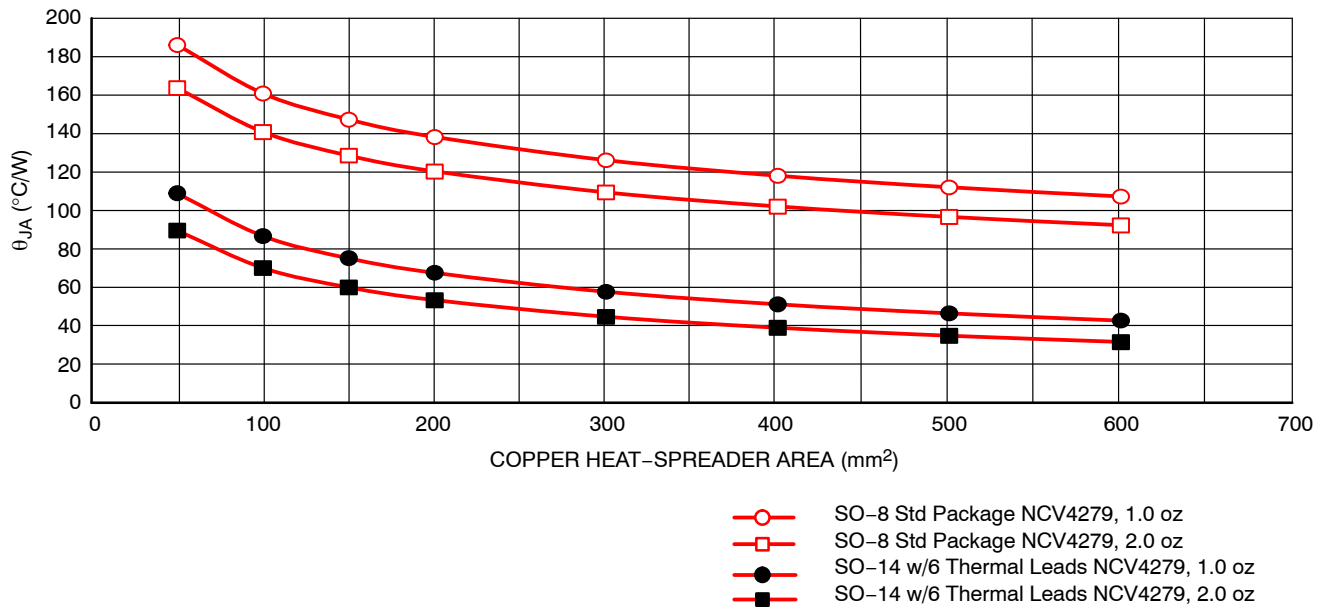


Figure 18. Junction-to-Ambient Thermal Resistance (θ_{JA}) vs. Heat Spreader Area

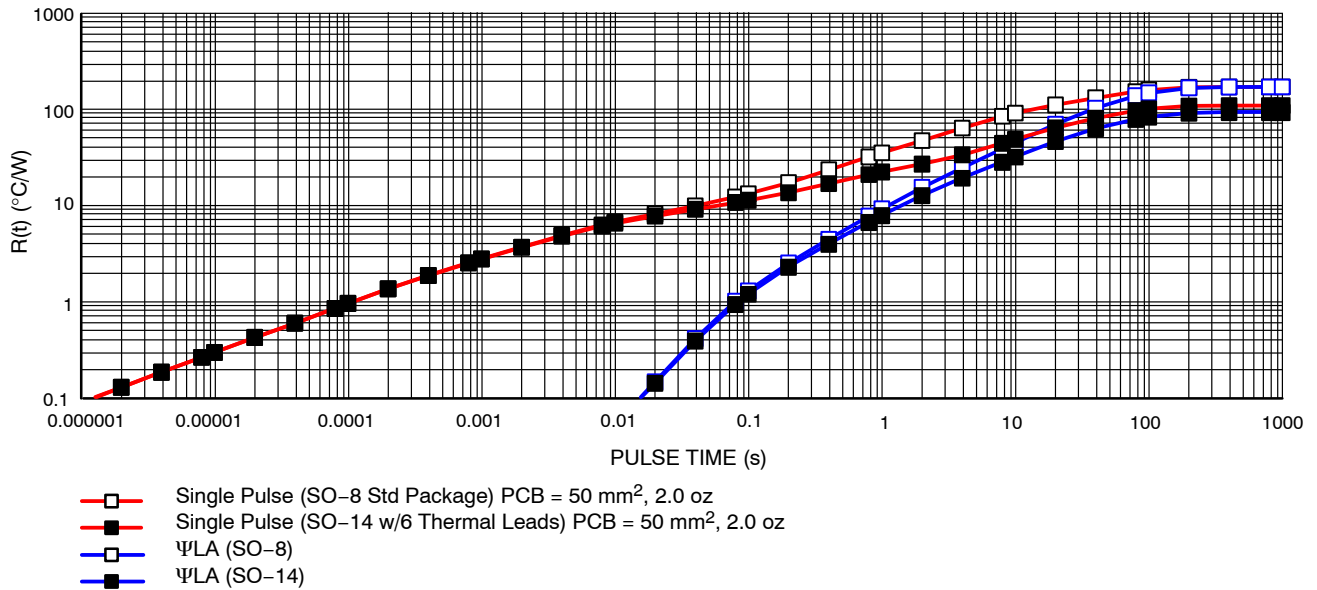


Figure 19. $R(t)$ vs. Pulse Time

SENSE INPUT (SI) / SENSE OUTPUT (SO) VOLTAGE MONITOR

An on-chip comparator is available to provide early warning to the microprocessor of a possible reset signal. The output is from an open collector driver. The reset signal typically turns the microprocessor off instantaneously. This can cause unpredictable results with the microprocessor. The signal received from the SO pin will allow the microprocessor time to complete its present task before shutting down. This function is performed by a comparator referenced to the band gap voltage. The actual trip point can be programmed externally using a resistor divider to the input monitor SI (Figure 20). The values for R_{SI1} and R_{SI2} are selected for a typical threshold of 1.20 V on the SI Pin.

SIGNAL OUTPUT

Figure 21 shows the SO Monitor timing waveforms as a result of the circuit depicted in Figure 20. As the output voltage (V_Q) falls, the monitor threshold ($V_{SI,Low}$), is crossed. This causes the voltage on the SO output to go low sending a warning signal to the microprocessor that a reset signal may occur in a short period of time. $T_{WARNING}$ is the time the microprocessor has to complete the function it is currently working on and get ready for the reset shutdown signal. When the voltage on the SO goes low and the RO stays high the current consumption is typically 560 μA at 1 mA load current.

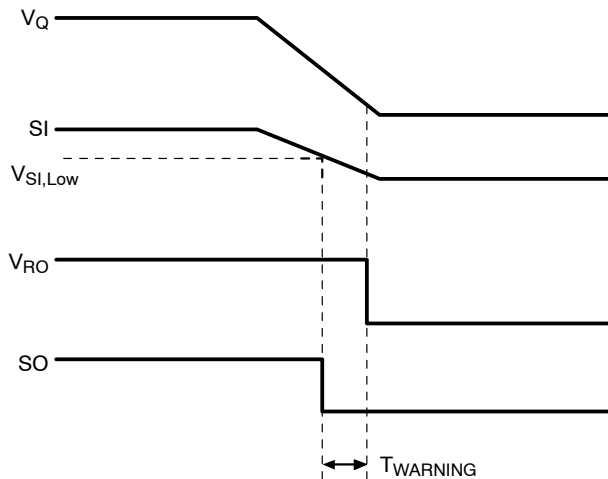


Figure 21. SO Warning Waveform Time Diagram

STABILITY CONSIDERATIONS

The input capacitor C_I in Figure 20 is necessary for compensating input line reactance. Possible oscillations caused by input inductance and input capacitance can be damped by using a resistor of approximately 1.0 Ω in series with C_I .

The output or compensation capacitor helps determine three main characteristics of a linear regulator: startup delay, load transient response and loop stability.

The capacitor value and type should be based on cost, availability, size and temperature constraints. The aluminum electrolytic capacitor is the least expensive

solution, but, if the circuit operates at low temperatures ($-25^{\circ}C$ to $-40^{\circ}C$), both the value and ESR of the capacitor will vary considerably. The capacitor manufacturer's data sheet usually provides this information.

The 10 μF output capacitor C_Q shown in Figure 20 should work for most applications; however, it is not necessarily the optimized solution. Stability is guaranteed at C_Q is min 2.2 μF and max ESR is 10 Ω . There is no min ESR limit which was proved with MURATA's ceramic caps GRM31MR71A225KA01 (2.2 μF , 10 V, X7R, 1206) and GRM31CR71A106KA01 (10 μF , 10 V, X7R, 1206) directly soldered between output and ground pins.

CALCULATING POWER DISSIPATION IN A SINGLE OUTPUT LINEAR REGULATOR

The maximum power dissipation for a single output regulator (Figure 20) is:

$$P_{D(max)} = [V_{I(max)} - V_{Q(min)}]I_{Q(max)} + V_{I(max)}I_q \quad (\text{eq. 4})$$

where:

$V_{I(max)}$ is the maximum input voltage,

$V_{Q(min)}$ is the minimum output voltage,

$I_{Q(max)}$ is the maximum output current for the application, and I_q is the quiescent current the regulator consumes at $I_{Q(max)}$.

Once the value of $P_{D(max)}$ is known, the maximum permissible value of $R_{\theta JA}$ can be calculated:

$$R_{\theta JA} = (150^{\circ}C - T_A) / P_D \quad (\text{eq. 5})$$

The value of $R_{\theta JA}$ can then be compared with those in the package section of the data sheet. Those packages with $R_{\theta JA}$'s less than the calculated value in equation 2 will keep the die temperature below $150^{\circ}C$. In some cases, none of the packages will be sufficient to dissipate the heat generated by the IC, and an external heatsink will be required. The current flow and voltages are shown in the Measurement Circuit Diagram.

HEATSINKS

A heatsink effectively increases the surface area of the package to improve the flow of heat away from the IC and into the surrounding air.

Each material in the heat flow path between the IC and the outside environment will have a thermal resistance. Like series electrical resistances, these resistances are summed to determine the value of $R_{\theta JA}$:

$$R_{\theta JA} = R_{\theta JC} + R_{\theta CS} + R_{\theta SA} \quad (\text{eq. 6})$$

where:

$R_{\theta JC}$ = the junction-to-case thermal resistance,

$R_{\theta CS}$ = the case-to-heat sink thermal resistance, and

$R_{\theta SA}$ = the heat sink-to-ambient thermal resistance.

$R_{\theta JC}$ appears in the package section of the data sheet. Like $R_{\theta JA}$, it too is a function of package type. $R_{\theta CS}$ and $R_{\theta SA}$ are functions of the package type, heatsink and the interface between them. These values appear in data sheets of heatsink manufacturers. Thermal, mounting, and heatsinking considerations are discussed in the ON Semiconductor application note AN1040/D, available on the ON Semiconductor website.

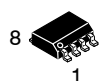
NCV4279A

ORDERING INFORMATION

Device	Output Voltage	Package	Shipping†
NCV4279A50D1G	5.0 V	SO-8 (Pb-Free)	98 Units/Rail
NCV4279A50D1R2G		SO-8 (Pb-Free)	2500 Tape & Reel
NCV4279A50D2G		SO-14 (Pb-Free)	55 Units/Rail
NCV4279A50D2R2G		SO-14 (Pb-Free)	2500 Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

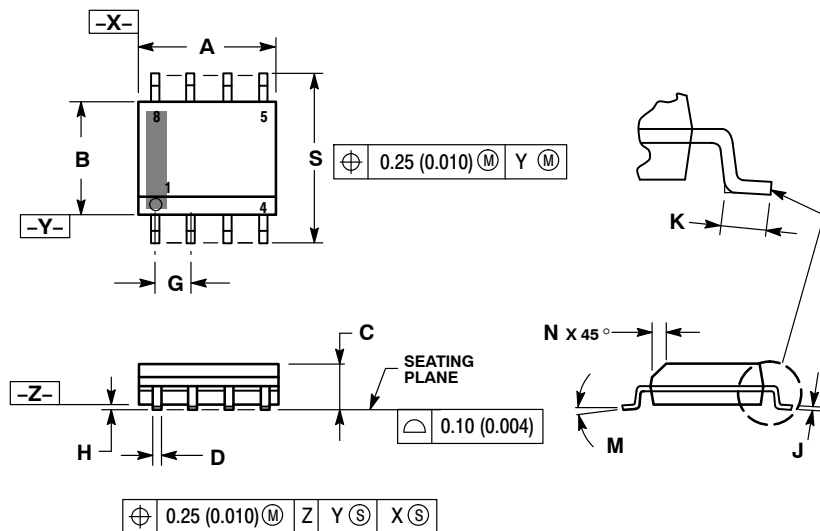
MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



SCALE 1:1

SOIC-8 NB
CASE 751-07
ISSUE AK

DATE 16 FEB 2011

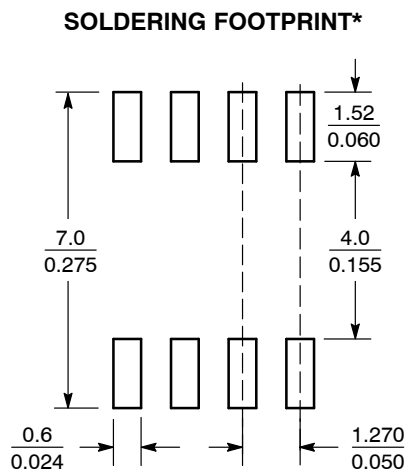


NOTES:

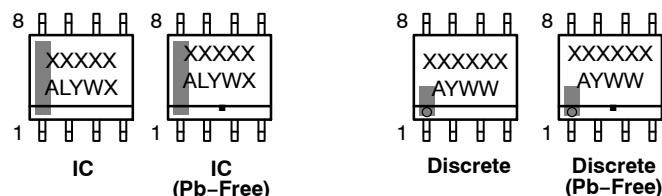
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. 751-01 THRU 751-06 ARE OBSOLETE. NEW STANDARD IS 751-07.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.80	5.00	0.189	0.197
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.053	0.069
D	0.33	0.51	0.013	0.020
G	1.27 BSC		0.050 BSC	
H	0.10	0.25	0.004	0.010
J	0.19	0.25	0.007	0.010
K	0.40	1.27	0.016	0.050
M	0°	8°	0°	8°
N	0.25	0.50	0.010	0.020
S	5.80	6.20	0.228	0.244

GENERIC MARKING DIAGRAM*



SCALE 6:1 (mm/inches)



XXXXXX = Specific Device Code
A = Assembly Location
L = Wafer Lot
Y = Year
W = Work Week
▪ = Pb-Free Package

XXXXXX = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week
▪ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLES ON PAGE 2

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CASE 751-07
ISSUE AK

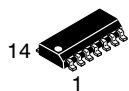
DATE 16 FEB 2011

STYLE 1: PIN 1. EMITTER 2. COLLECTOR 3. COLLECTOR 4. EMITTER 5. EMITTER 6. BASE 7. BASE 8. EMITTER	STYLE 2: PIN 1. COLLECTOR, DIE, #1 2. COLLECTOR, #1 3. COLLECTOR, #2 4. COLLECTOR, #2 5. BASE, #2 6. EMITTER, #2 7. BASE, #1 8. EMITTER, #1	STYLE 3: PIN 1. DRAIN, DIE #1 2. DRAIN, #1 3. DRAIN, #2 4. DRAIN, #2 5. GATE, #2 6. SOURCE, #2 7. GATE, #1 8. SOURCE, #1	STYLE 4: PIN 1. ANODE 2. ANODE 3. ANODE 4. ANODE 5. ANODE 6. ANODE 7. ANODE 8. COMMON CATHODE
STYLE 5: PIN 1. DRAIN 2. DRAIN 3. DRAIN 4. DRAIN 5. GATE 6. GATE 7. SOURCE 8. SOURCE	STYLE 6: PIN 1. SOURCE 2. DRAIN 3. DRAIN 4. SOURCE 5. SOURCE 6. GATE 7. GATE 8. SOURCE	STYLE 7: PIN 1. INPUT 2. EXTERNAL BYPASS 3. THIRD STAGE SOURCE 4. GROUND 5. DRAIN 6. GATE 3 7. SECOND STAGE Vd 8. FIRST STAGE Vd	STYLE 8: PIN 1. COLLECTOR, DIE #1 2. BASE, #1 3. BASE, #2 4. COLLECTOR, #2 5. COLLECTOR, #2 6. EMITTER, #2 7. EMITTER, #1 8. COLLECTOR, #1
STYLE 9: PIN 1. EMITTER, COMMON 2. COLLECTOR, DIE #1 3. COLLECTOR, DIE #2 4. EMITTER, COMMON 5. EMITTER, COMMON 6. BASE, DIE #2 7. BASE, DIE #1 8. EMITTER, COMMON	STYLE 10: PIN 1. GROUND 2. BIAS 1 3. OUTPUT 4. GROUND 5. GROUND 6. BIAS 2 7. INPUT 8. GROUND	STYLE 11: PIN 1. SOURCE 1 2. GATE 1 3. SOURCE 2 4. GATE 2 5. DRAIN 2 6. DRAIN 2 7. DRAIN 1 8. DRAIN 1	STYLE 12: PIN 1. SOURCE 2. SOURCE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN
STYLE 13: PIN 1. N.C. 2. SOURCE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN	STYLE 14: PIN 1. N-SOURCE 2. N-GATE 3. P-SOURCE 4. P-GATE 5. P-DRAIN 6. P-DRAIN 7. N-DRAIN 8. N-DRAIN	STYLE 15: PIN 1. ANODE 1 2. ANODE 1 3. ANODE 1 4. ANODE 1 5. CATHODE, COMMON 6. CATHODE, COMMON 7. CATHODE, COMMON 8. CATHODE, COMMON	STYLE 16: PIN 1. EMITTER, DIE #1 2. BASE, DIE #1 3. EMITTER, DIE #2 4. BASE, DIE #2 5. COLLECTOR, DIE #2 6. COLLECTOR, DIE #2 7. COLLECTOR, DIE #1 8. COLLECTOR, DIE #1
STYLE 17: PIN 1. VCC 2. V2OUT 3. V1OUT 4. TXE 5. RXE 6. VEE 7. GND 8. ACC	STYLE 18: PIN 1. ANODE 2. ANODE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. CATHODE 8. CATHODE	STYLE 19: PIN 1. SOURCE 1 2. GATE 1 3. SOURCE 2 4. GATE 2 5. DRAIN 2 6. MIRROR 2 7. DRAIN 1 8. MIRROR 1	STYLE 20: PIN 1. SOURCE (N) 2. GATE (N) 3. SOURCE (P) 4. GATE (P) 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN
STYLE 21: PIN 1. CATHODE 1 2. CATHODE 2 3. CATHODE 3 4. CATHODE 4 5. CATHODE 5 6. COMMON ANODE 7. COMMON ANODE 8. CATHODE 6	STYLE 22: PIN 1. I/O LINE 1 2. COMMON CATHODE/VCC 3. COMMON CATHODE/VCC 4. I/O LINE 3 5. COMMON ANODE/GND 6. I/O LINE 4 7. I/O LINE 5 8. COMMON ANODE/GND	STYLE 23: PIN 1. LINE 1 IN 2. COMMON ANODE/GND 3. COMMON ANODE/GND 4. LINE 2 IN 5. LINE 2 OUT 6. COMMON ANODE/GND 7. COMMON ANODE/GND 8. LINE 1 OUT	STYLE 24: PIN 1. BASE 2. EMITTER 3. COLLECTOR/ANODE 4. COLLECTOR/ANODE 5. CATHODE 6. CATHODE 7. COLLECTOR/ANODE 8. COLLECTOR/ANODE
STYLE 25: PIN 1. VIN 2. N/C 3. REXT 4. GND 5. IOUT 6. IOUT 7. IOUT 8. IOUT	STYLE 26: PIN 1. GND 2. dv/dt 3. ENABLE 4. ILIMIT 5. SOURCE 6. SOURCE 7. SOURCE 8. VCC	STYLE 27: PIN 1. ILIMIT 2. OVLO 3. UVLO 4. INPUT+ 5. SOURCE 6. SOURCE 7. SOURCE 8. DRAIN	STYLE 28: PIN 1. SW_TO_GND 2. DASIC_OFF 3. DASIC_SW_DET 4. GND 5. V_MON 6. VBULK 7. VBULK 8. VIN
STYLE 29: PIN 1. BASE, DIE #1 2. EMITTER, #1 3. BASE, #2 4. EMITTER, #2 5. COLLECTOR, #2 6. COLLECTOR, #2 7. COLLECTOR, #1 8. COLLECTOR, #1	STYLE 30: PIN 1. DRAIN 1 2. DRAIN 1 3. GATE 2 4. SOURCE 2 5. SOURCE 1/DRAIN 2 6. SOURCE 1/DRAIN 2 7. SOURCE 1/DRAIN 2 8. GATE 1		

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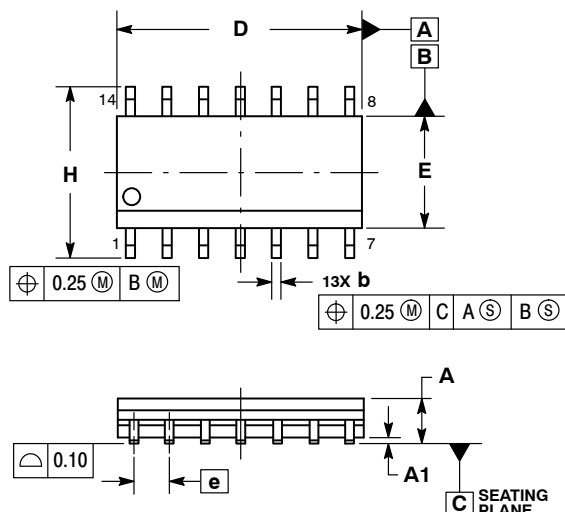
MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



SCALE 1:1

SOIC-14 NB
CASE 751A-03
ISSUE L

DATE 03 FEB 2016

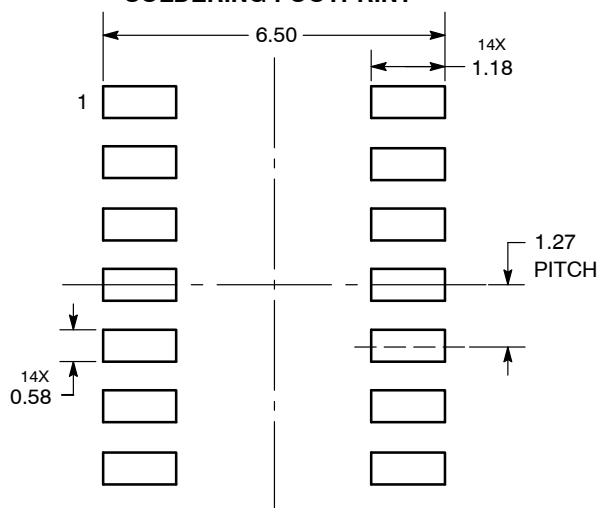


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF AT MAXIMUM MATERIAL CONDITION.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSIONS.
5. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	1.35	1.75	0.054	0.068
A1	0.10	0.25	0.004	0.010
A3	0.19	0.25	0.008	0.010
b	0.35	0.49	0.014	0.019
D	8.55	8.75	0.337	0.344
E	3.80	4.00	0.150	0.157
e	1.27 BSC		0.050 BSC	
H	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.019
L	0.40	1.25	0.016	0.049
M	0°	7°	0°	7°

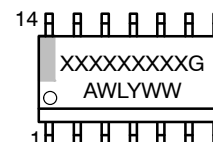
SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



XXXXXX = Specific Device Code
A = Assembly Location
WL = Wafer Lot
Y = Year
WW = Work Week
G = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

STYLES ON PAGE 2

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SOIC-14
CASE 751A-03
ISSUE L

DATE 03 FEB 2016

STYLE 1:
PIN 1. COMMON CATHODE
2. ANODE/CATHODE
3. ANODE/CATHODE
4. NO CONNECTION
5. ANODE/CATHODE
6. NO CONNECTION
7. ANODE/CATHODE
8. ANODE/CATHODE
9. ANODE/CATHODE
10. NO CONNECTION
11. ANODE/CATHODE
12. ANODE/CATHODE
13. NO CONNECTION
14. COMMON ANODE

STYLE 2:
CANCELLED

STYLE 3:
PIN 1. NO CONNECTION
2. ANODE
3. ANODE
4. NO CONNECTION
5. ANODE
6. NO CONNECTION
7. ANODE
8. ANODE
9. ANODE
10. NO CONNECTION
11. ANODE
12. ANODE
13. NO CONNECTION
14. COMMON CATHODE

STYLE 4:
PIN 1. NO CONNECTION
2. CATHODE
3. CATHODE
4. NO CONNECTION
5. CATHODE
6. NO CONNECTION
7. CATHODE
8. CATHODE
9. CATHODE
10. NO CONNECTION
11. CATHODE
12. CATHODE
13. NO CONNECTION
14. COMMON ANODE

STYLE 5:
PIN 1. COMMON CATHODE
2. ANODE/CATHODE
3. ANODE/CATHODE
4. ANODE/CATHODE
5. ANODE/CATHODE
6. NO CONNECTION
7. COMMON ANODE
8. COMMON CATHODE
9. ANODE/CATHODE
10. ANODE/CATHODE
11. ANODE/CATHODE
12. ANODE/CATHODE
13. NO CONNECTION
14. COMMON ANODE

STYLE 6:
PIN 1. CATHODE
2. CATHODE
3. CATHODE
4. CATHODE
5. CATHODE
6. CATHODE
7. CATHODE
8. ANODE
9. ANODE
10. ANODE
11. ANODE
12. ANODE
13. ANODE
14. ANODE

STYLE 7:
PIN 1. ANODE/CATHODE
2. COMMON ANODE
3. COMMON CATHODE
4. ANODE/CATHODE
5. ANODE/CATHODE
6. ANODE/CATHODE
7. ANODE/CATHODE
8. ANODE/CATHODE
9. ANODE/CATHODE
10. ANODE/CATHODE
11. COMMON CATHODE
12. COMMON ANODE
13. ANODE/CATHODE
14. ANODE/CATHODE

STYLE 8:
PIN 1. COMMON CATHODE
2. ANODE/CATHODE
3. ANODE/CATHODE
4. NO CONNECTION
5. ANODE/CATHODE
6. ANODE/CATHODE
7. COMMON ANODE
8. COMMON ANODE
9. ANODE/CATHODE
10. ANODE/CATHODE
11. NO CONNECTION
12. ANODE/CATHODE
13. ANODE/CATHODE
14. COMMON CATHODE

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